

■ DESCRIPTION

The 4410 is the N-Channel logic enhancement mode power field effect transistor is produced using high cell density advanced trench technology..

This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits where high-side switching

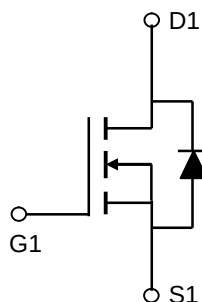
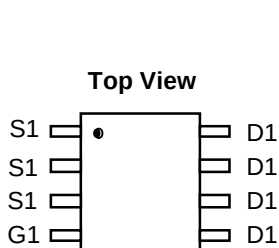
■ FEATURE

- ◆ 30V/18 A, $R_{DS(ON)}=4.5m\Omega$ (typ.)@VGS=10V
- ◆ 30V/15A, $R_{DS(ON)}=6.0m\Omega$ (typ.)@VGS= 4.5V
- ◆ Super high design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and Maximum DC current capability
- ◆ Full RoHS compliance
- ◆ SOP8 package design
- ◆ 100% UIS Tested
- ◆ 100% Rg tested

■ APPLICATIONS

- ◆ Power Management
- ◆ Portable Equipment
- ◆ DC/DC Converter
- ◆ Load Switch
- ◆ DSC
- ◆ LCD Display inverter

■ PIN CONFIGURATION



■ **ABSOLUTE MAXIMUM RATINGS** ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

Symbol	Parameter		Typical	Unit
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		± 12	V
I_D	Continuous Drain Current ($T_J=150^\circ\text{C}$)	$V_{GS}=10\text{V}$	18	A
I_{DM}	Pulsed Drain Current		80	A
I_S	Continuous Source Current (Diode Conduction)		4.0	A
P_D	Power Dissipation	$T_A=25^\circ\text{C}$	3.0	W
		$T_A=70^\circ\text{C}$	2.1	
T_J	Operation Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55~+150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient		62.5	$^\circ\text{C/W}$

**Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress rating only and functional device operation is not implied**

■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^\circ\text{C}$ Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = 250uA	30			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 250uA	1.0		2.0	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±12V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24V, V _{GS} =0			1	uA
		V _{DS} = 24V, V _{GS} =0 T _J =85℃			30	
R _{DS(ON)}	Drain-Source On-Resistance	V _{GS} = 10V, I _D = 18 A		4.5	5.5	mΩ
		V _{GS} = 4.5V, I _D = 15 A		6	6.8	
Source-Drain Diode						
V _{SD}	Diode Forward Voltage	I _S = 2.0A, V _{GS} =0V		0.7	1.3	V
Dynamic Parameters						
Q _g	Total Gate Charge	V _{DS} = 15V V _{GS} = 10V I _D = 18 A		81.6		nC
Q _{gs}	Gate-Source Charge			12.5		
Q _{gd}	Gate-Drain Charge			16.0		
C _{iss}	Input Capacitance	V _{DS} = 25V V _{GS} =0V f=1MHz		9720		pF
C _{oss}	Output Capacitance			710		
C _{rss}	Reverse Transfer Capacitance			423		
T _{d(on)}	Turn-On Time	V _{DS} = 15V R _L =1Ω I _D = 1A V _{GEN} = 10V R _G =6Ω		11		nS
T _r				8.5		
T _{d(off)}	Turn-Off Time			79		
T _f				13		

Note: 1. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

2. Static parameters are based on package level with recommended wire bonding

TYPICAL CHARACTERISTICS (25 °C Unless Note)

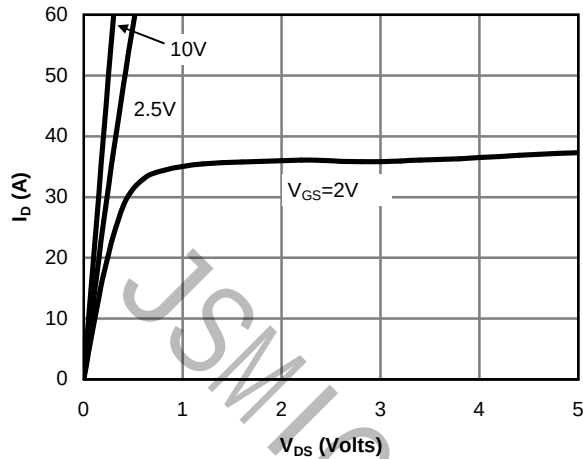


Fig 1: On-Region Characteristics

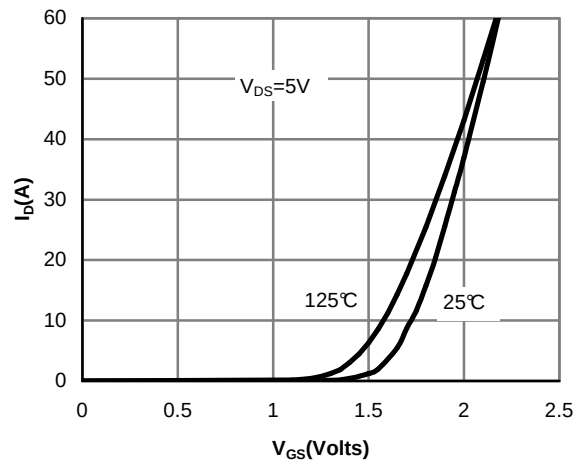


Figure 2: Transfer Characteristics

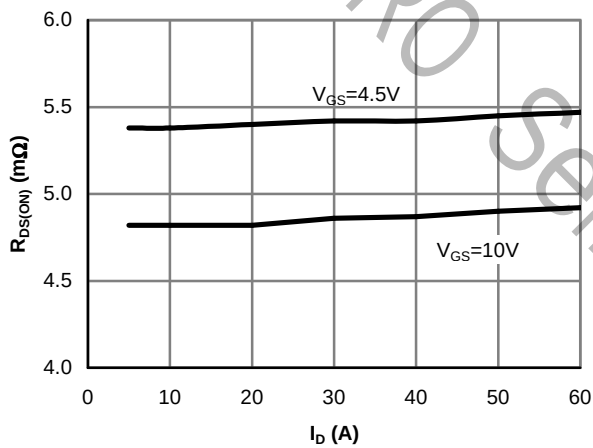


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

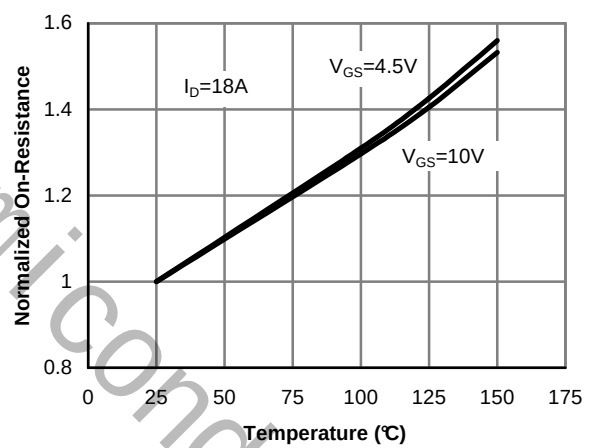


Figure 4: On-Resistance vs. Junction Temperature

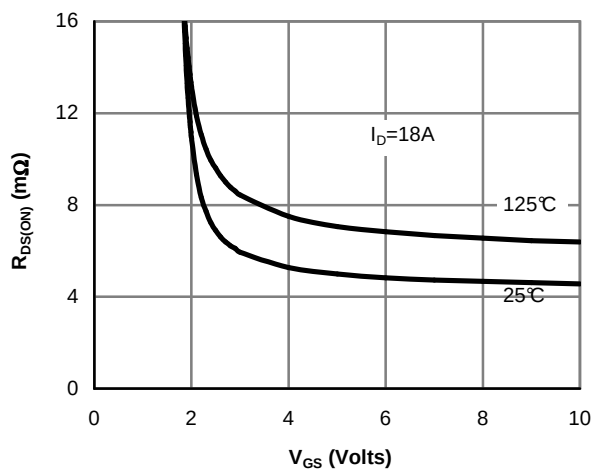


Figure 5: On-Resistance vs. Gate-Source Voltage

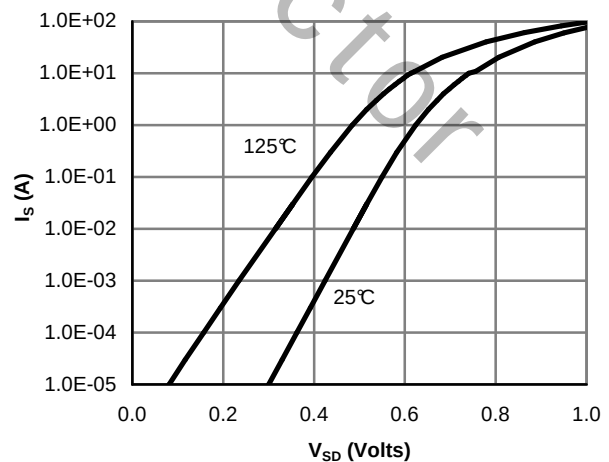


Figure 6: Body-Diode Characteristics

■ TYPICAL CHARACTERISTICS (continuous)

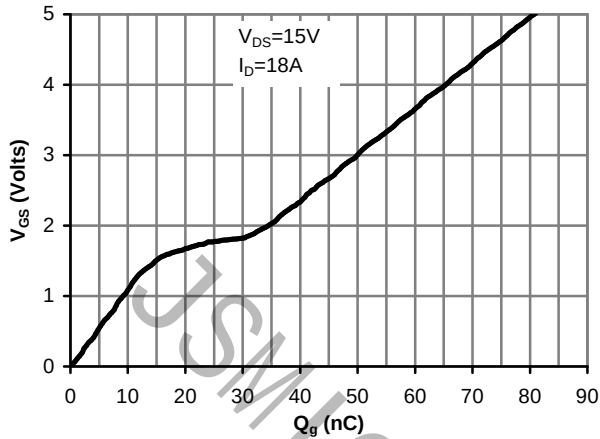


Figure 7: Gate-Charge Characteristics

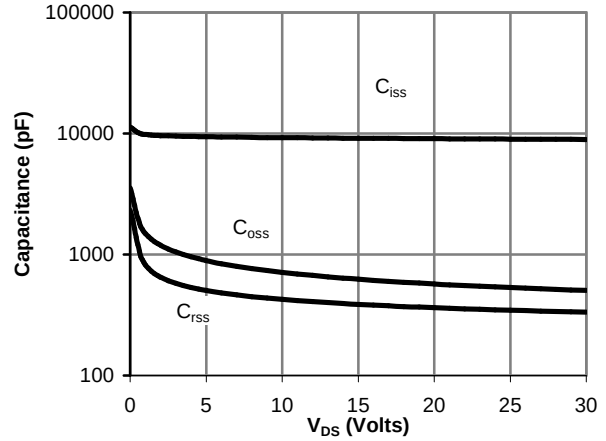


Figure 8: Capacitance Characteristics

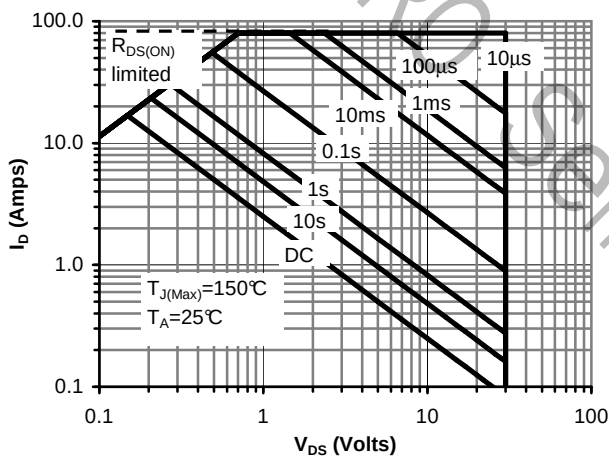


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

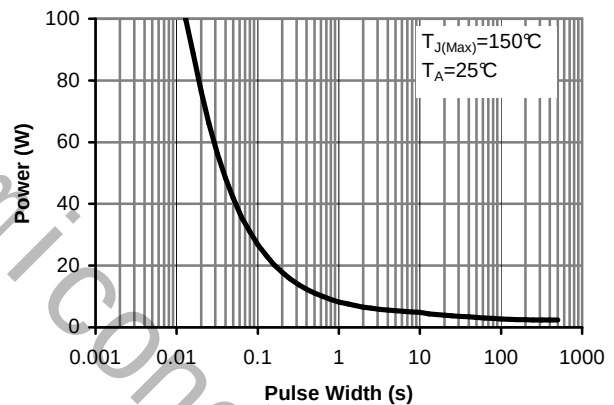


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

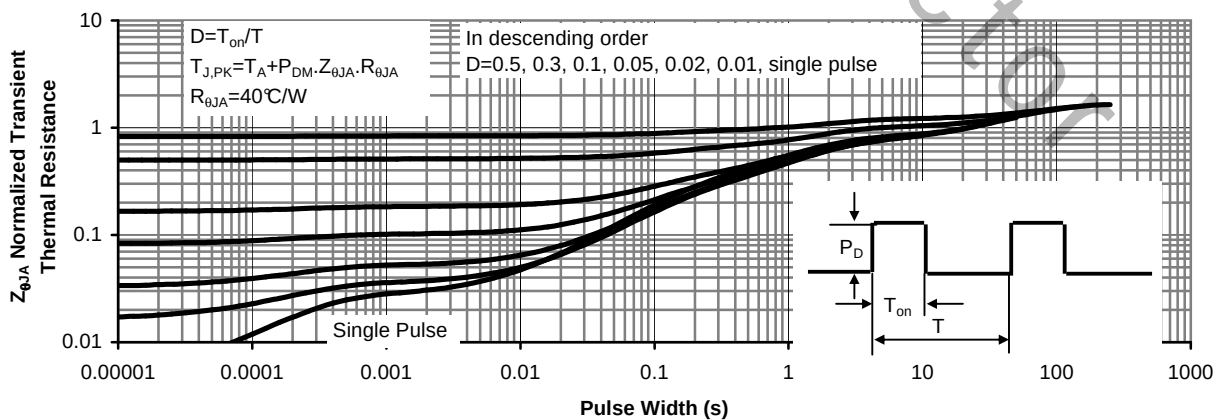
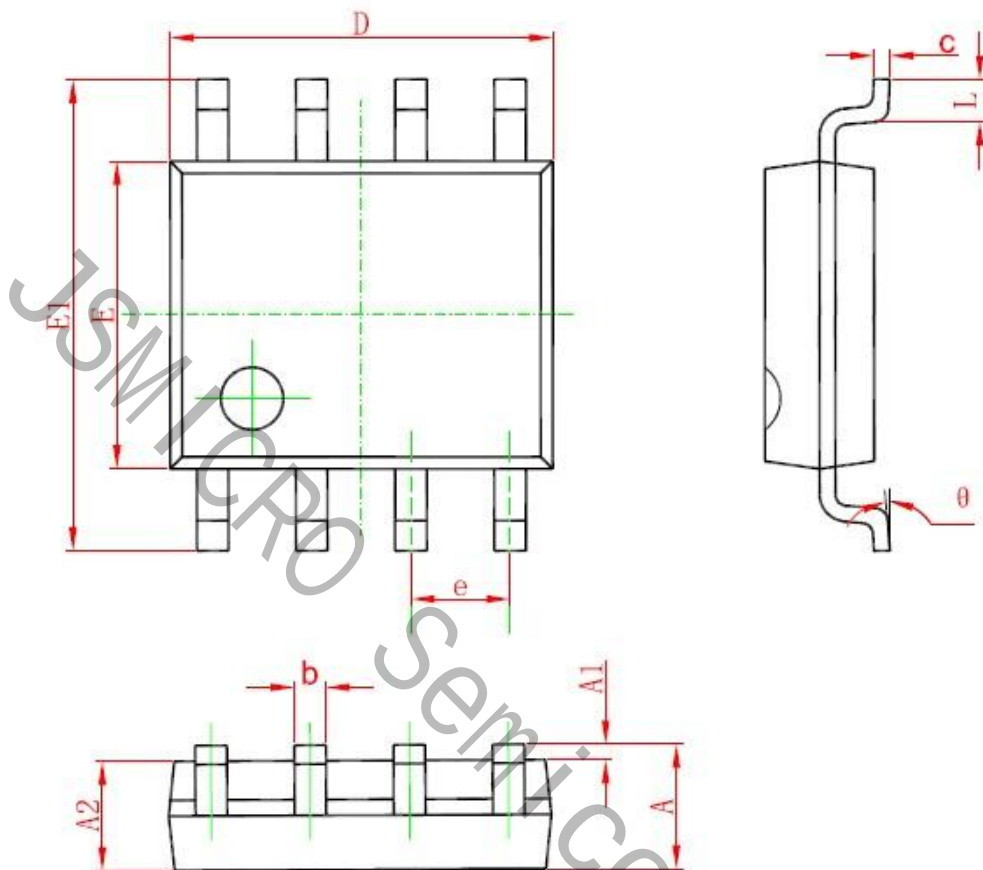


Figure 11: Normalized Maximum Transient Thermal Impedance

■ SOP8 PACKAGE OUTLINE DIMENSIONS

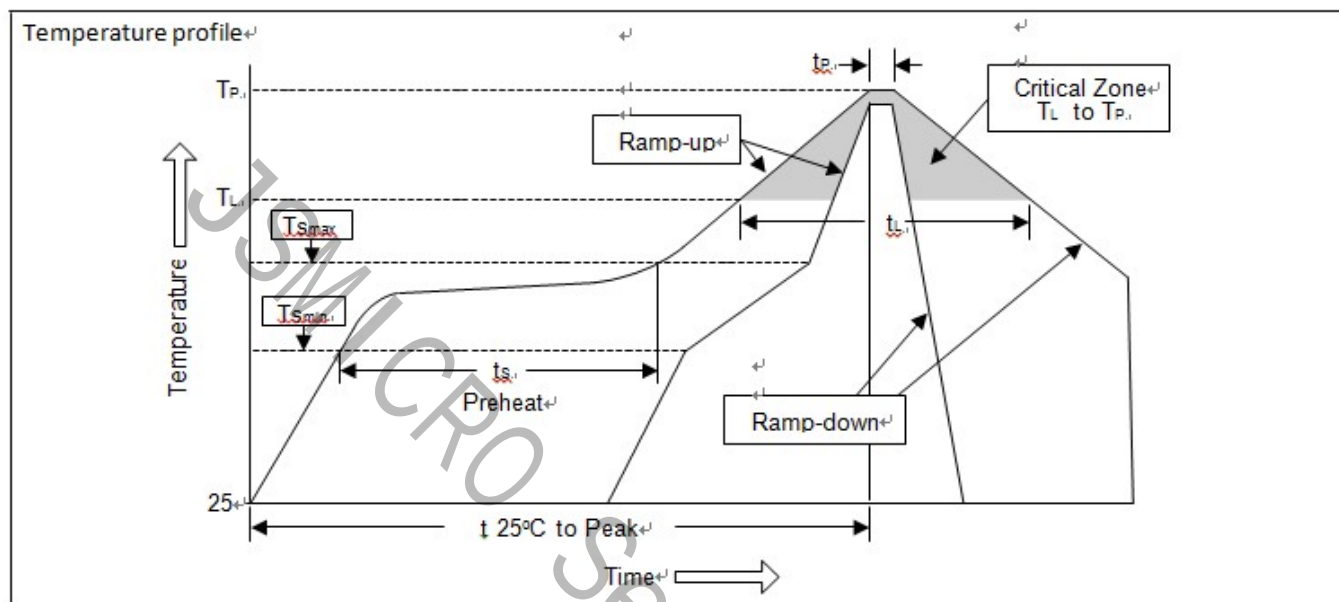


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

■ SOLDERING METHODS FOR UNIVERCHIP

Storage environment Temperature=10°C~35°C Humidity=65%±15%

Reflow soldering of surface mount device



Profile Feature	Sn-Pb Eutectic Assembly	Pb free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
-Temperature Min (T_{smin})	100°C	150°C
-Temperature Max (T_{smax})	150°C	200°C
-Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{smax} to T_L		
-Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above		
-Temperature (T_L)	183°C	217°C
-Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<6 minutes

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C±5°C	5sec±1sec
Pb-Free device	260°C+0/-5°C	5sec±1sec

JSMICRO Semiconductor